VERSION WITH MARKINGS TO SHOW CHANGES MADE

Claims 1, 3, 12 and 13 have been rewritten and new claims 31 and 32 have been added.

1. (Amended) A semiconductor device comprising:

a solder mask;

a die; and

an adhesive layer between said die and said solder mask, wherein said adhesive layer [is at least partially cured at a temperature below about 100°C] comprises a material that remains voidless after outgassing from said solder mask.

3. (Amended) The semiconductor device of claim 1, wherein said adhesive layer is fully cured at a temperature below about 100°C.

12. (Amended) A semiconductor device comprising:

a solder mask;

a die;

electrical contacts on said solder mask and said die, each said contact on said die being wire bonded to a respective said contact on said mask, said electrical contacts being devoid of contamination caused by outgassing from said solder mask; and

an adhesive layer affixing said die to said solder mask[, wherein said adhesive layer is cured at a temperature between about 20°C and about 50°C higher than a glassy temperature of said adhesive layer and said curing temperature is below about 100°C].

13. (Amended) The semiconductor device of claim 12, wherein said adhesive layer is at least partially cured at a temperature below about 100°C.

31. (New) The semiconductor device of claim 1, wherein said adhesive layer is at least partially cured at a temperature below about 100°C.

32. (New) The semiconductor device of claim 12, wherein said adhesive layer is cured at a temperature between about 20°C and about 50°C higher than a glassy temperature of said adhesive layer and said curing temperature is below about 100°C.